NSN 5961-01-180-1944

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nclosure Material:
Metal all transistor
Overall Length:
1.573 inches 2nd transistor
Overall Height:
0.340 inches 1st transistor
Overall Width:
1.050 inches 2nd transistor
End Application:
F-16 a/b aircraft
Mounting Facility Quantity:
2 all transistor
nternal Configuration:
Junction contact all transistor
Electrode Internally-electrically Connected To Case:
Collector all transistor
nternal Junction Configuration:
Pnp 1st transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Unthreaded hole all transistor
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
275.0 collector to base voltage/static/emitter open 1st transistor and 225.0 collector to emitter voltage/static/base open 1st transistor and
6.0 emitter to base voltage, static, collector open 1st transistor
Current Rating Per Characteristic:
20.00 amperes source cutoff current 2nd transistor and 50.00 amperes source cutoff current 2nd transistor
Power Rating Per Characteristic:
250.0 watts small-signal input power, common-collector preset 2nd transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air 1st transistor
Terminal Type And Quantity:
2 pin all transistor and 1 case all transistor
Shelf Life:
N/a
Unit Of Measure:
-
Demilitarization:

No

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